

GS321LV

Single Low Voltage, Low Noise, 2.2MHz, Rail-to-Rail Input/Output, General Purpose CMOS Operational Amplifiers

Product Description

The GS321LV are low voltage CMOS operational amplifiers, low power, low noise, internally frequency compensated CMOS operational amplifiers. It also features wider bandwidth, lower quiescent and lower offset than legacy LMV operational amplifier family.

They operate from a single power supply ranging from +1.8V to +7.0V. Operation from split power supplies is also possible and the low power supply current drain is independent of the magnitude of the power supply voltage.

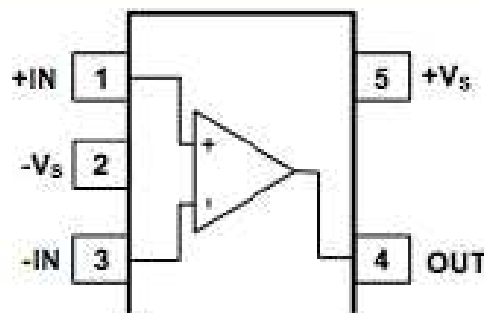
Features

- Wide power supply range : +1.8V to +7.0V
- Gain-bandwidth product, GBP(typ)=2.2MHz
- Low Noise Voltage Density : $17\text{nV}/\sqrt{\text{Hz}}$
- Low quiescent current per amplifier : 60 μA
- Low input bias current : 1pA
- Low Offset : $V_{os}(\text{typ})=1\text{mV}$, $I_{os}(\text{typ})=1\text{pA}$
- Unity Gain Stable
- Packages : SOT-23-5L
- RoHS Compliant, 100%Pb & Halogen Free

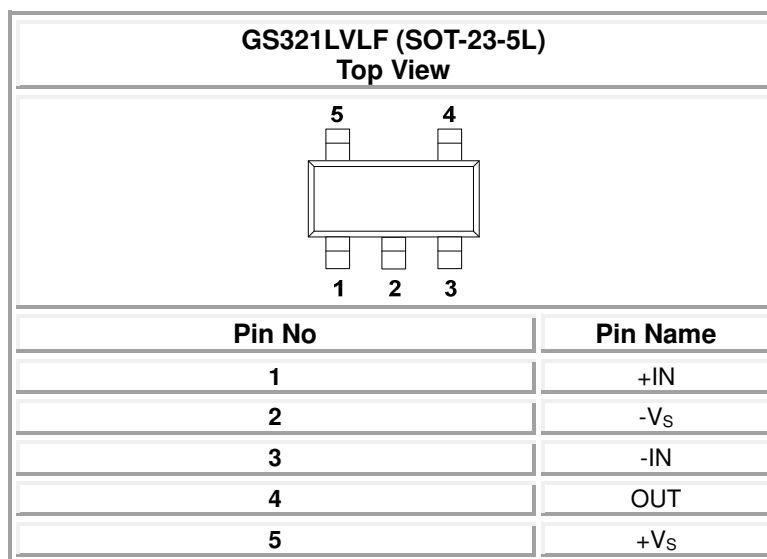
Applications

- Chargers
- Power supplies
- Industrial: controls, instruments
- Desktops
- Communications infrastructure

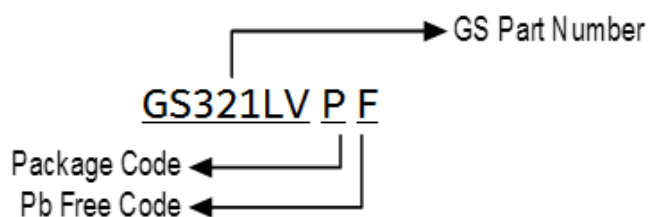
Block Diagram



Pin Assignments

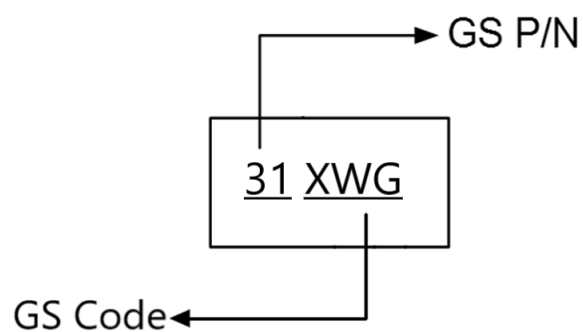


Ordering Information



Device	Package	Quantity Reel
GS321LVLF	SOT-23-5L	3000PCS

Marking Information



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	7.5	V
V_{IN}	Input voltage	-0.5 to 7.5	V
	Output short-circuit duration	Infinite	
I_{IN}	Input current : V_{IN} driven negative Input current : V_{IN} driven positive above	5mA in DC or 50mA in AC (duty cycle=10%, T=1s)	mA
T_{OPA}	Operating free-air temperature range	-40 to +85	°C
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C
θ_{JA}	Thermal resistance junction to ambient	190	°C/W
ESD	Human body mode (HBM)	8000	V
	Machine mode (MM)	400	

Note 1. Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Note 2. This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. Recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

Electrical Characteristics

$V_S=+5V$, $T_A=25^\circ C$, $V_{CM}=V_S/2$, $R_L=600\Omega$, unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{OS}	Input offset voltage			1	3.7	mV
I_B	Input bias current			1		pA
I_{OS}	Input offset current			1		pA
V_{CM}	Common-mode voltage range	$V_S=6.6V$		-0.1 to +6.7		V
CMRR	Common-mode rejection ratio	$V_S=5.5V$, $V_{CM}=-0.1V$ to 4.8V	75	80		dB
		$V_S=5.5V$, $V_{CM}=-0.1V$ to 5.6V	64	75		dB
A_{OL}	Open-loop voltage gain	$R_L=600\Omega$, $V_O=0.15V$ to 4.85V	70	80		dB
		$R_L=10K\Omega$, $V_O=0.05V$ to 4.95V	75	85		dB
$\Delta V_{OS}/\Delta T$	input offset voltage drift			2.1		$\mu V/^\circ C$
	Output voltage swing from rail	$R_L=600\Omega$		0.1		V
		$R_L=100K\Omega$		0.015		V
I_{OUT}	Output current		20	25		mA
	Operating voltage range		1.8		7.0	V
PSRR	Power supply rejection ratio	$V_S=+2.5V$ to +5.5V $V_{CM}=(-V_S)+0.5V$	70	80		dB
I_Q	Quiescent current	$I_{OUT}=0A$	60	85		μA

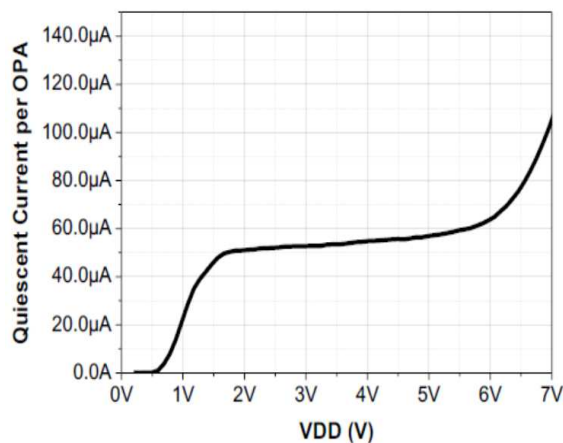
Electrical Characteristics (Continue)

$V_S=+5V$, $T_A=25^{\circ}C$, $V_{CM}=V_S/2$, $R_L=600\Omega$, unless otherwise noted

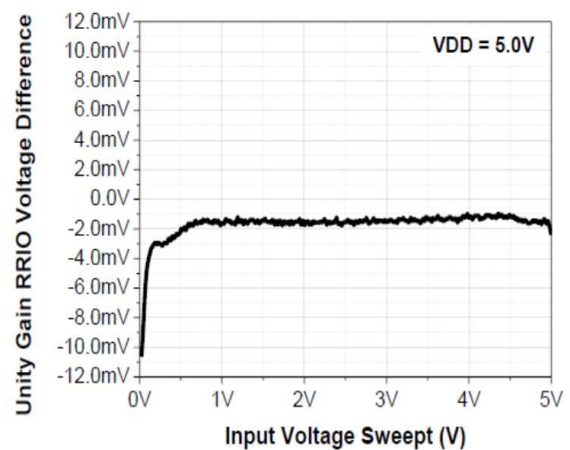
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
GBP	Gain-bandwidth product	$R_L=600\Omega$		2.2		MHz
Φ_o	Phase margin			63.5		deg
BW _P	Full power bandwidth	<1% distortion		400		KHz
SR	Slew rate	$G=+1, 2V$ Output step		1.04		V/ μs
t_s	Settling time to 0.1%	$G=+1, 2V$ Output step		0.36		μs
	Overload recovery time	V_{IN} Gain= V_S		0.4		μs
	Voltage noise density	$f=1KHz$		17		nV/ $\sqrt{Hz}$
		$f=10KHz$		11		nV/ $\sqrt{Hz}$

Typical Performance Characteristics

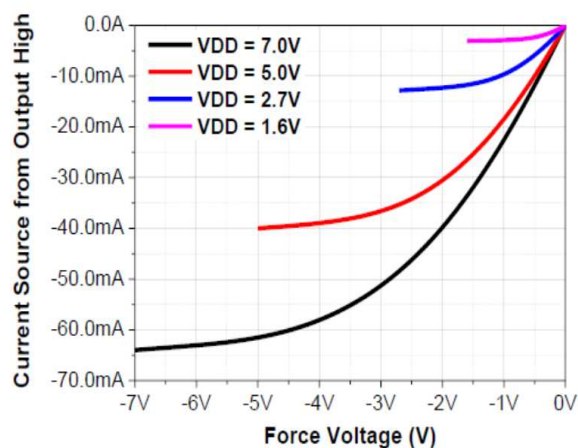
Quiescent Current vs. Supply Voltage



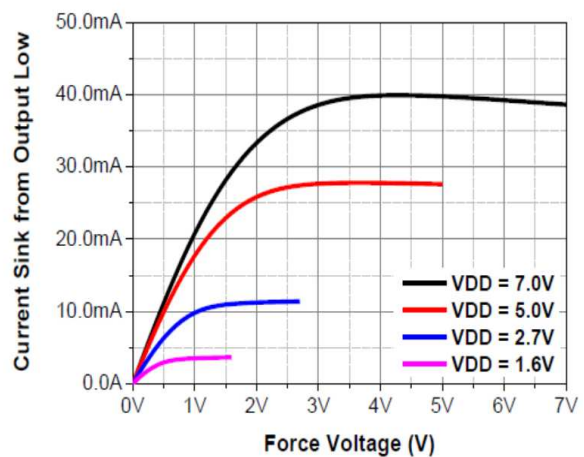
Rail Input to Rail Output Difference



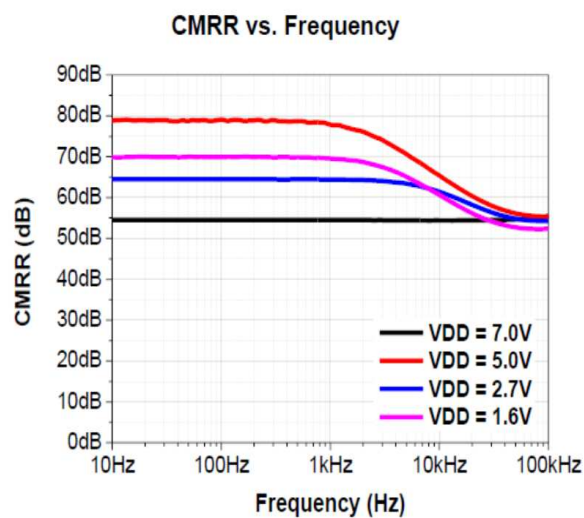
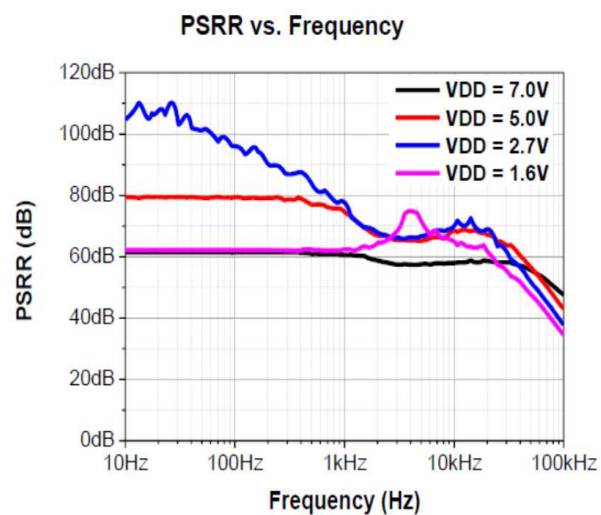
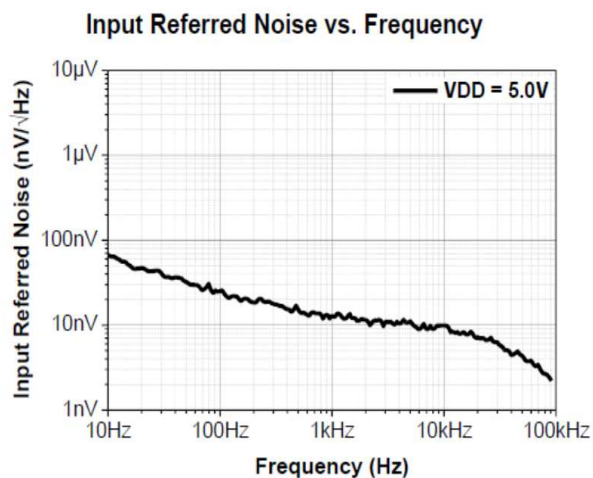
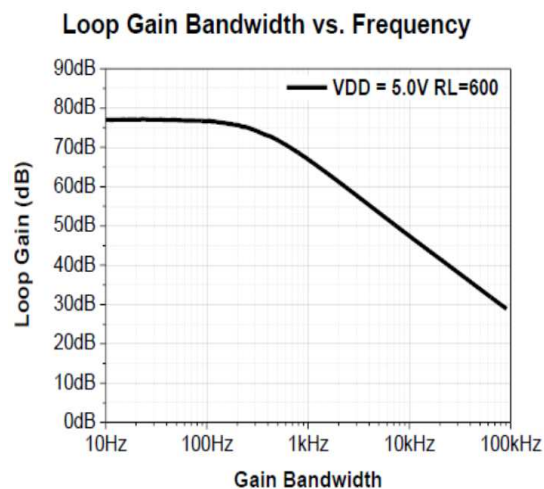
Output Voltage vs. Output Current Source



Output Voltage vs. Output Current Sink

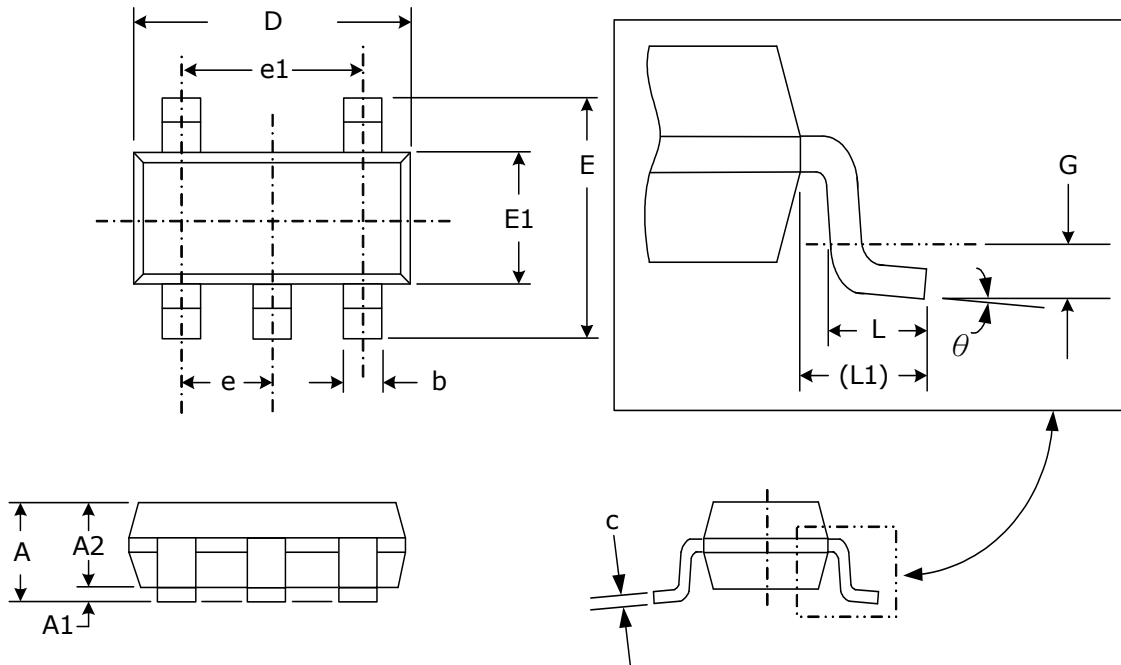


Typical Performance Characteristics (Continue)



Package Dimension

SOT-23-5L



Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.95	1.45	.037	.057
A1	0.05	0.15	.002	.006
A2	0.90	1.30	.035	.051
b	0.30	0.50	.012	.020
c	0.08	0.20	.003	.008
D	2.80	3.00	.110	.118
E	2.60	3.00	.102	.118
E1	1.50	1.70	.059	.067
e	0.95 (TYP)		.037 (TYP)	
e1	1.90 (TYP)		.075 (TYP)	
L	0.35	0.55	.014	.022
L1	0.60 (TYP)		.024 (TYP)	
G	0.25 (TYP)		.010 (TYP)	
Y	08	88	08	88

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